

FIG. 1
(PRIOR ART)

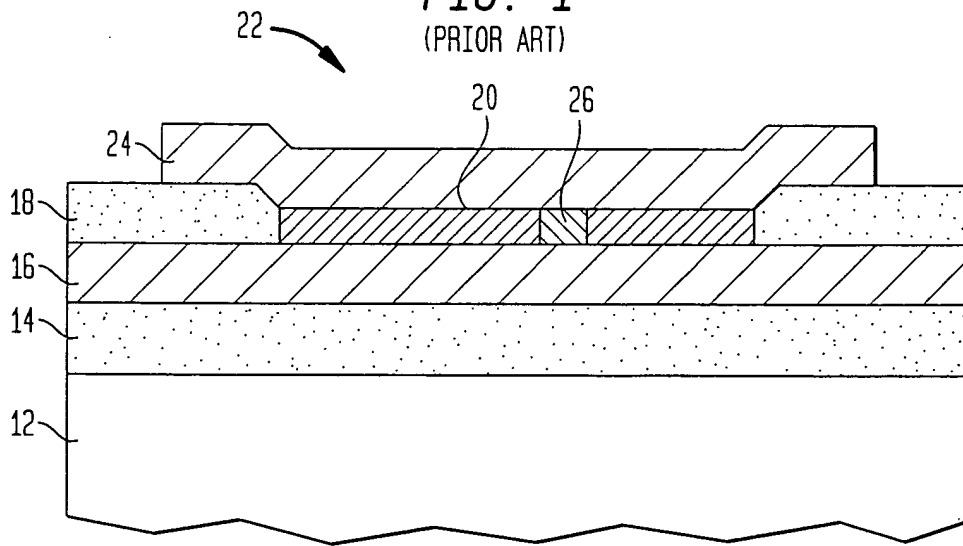


FIG. 2a

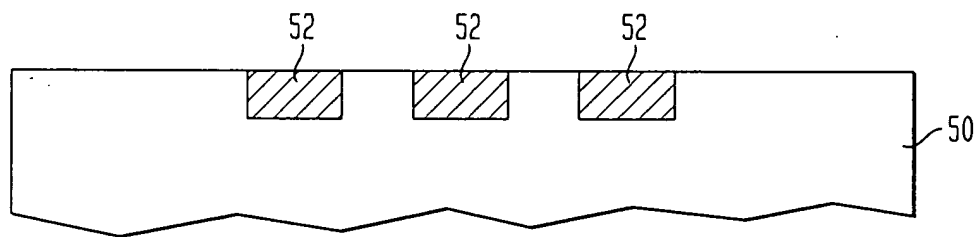


FIG. 2b

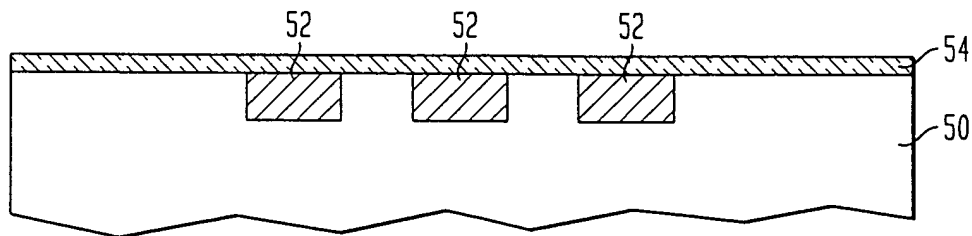


FIG. 2c

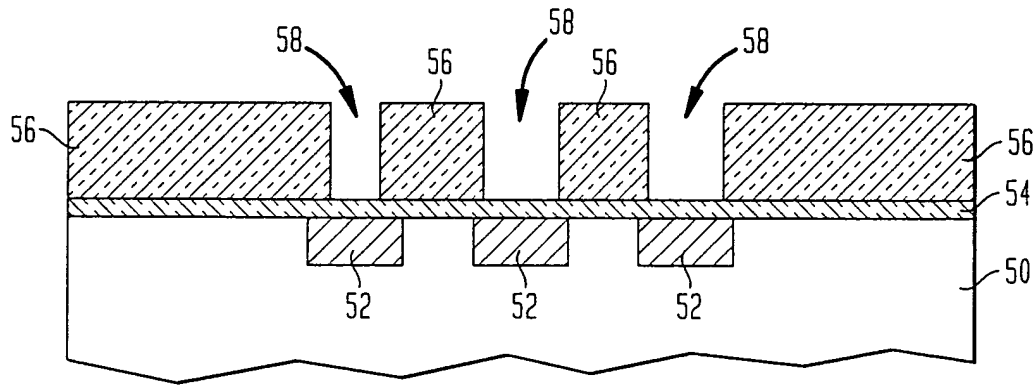


FIG. 2d

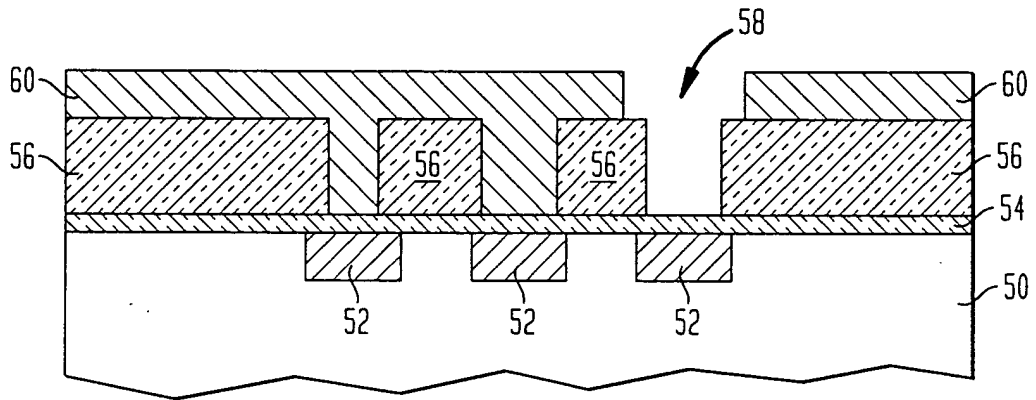
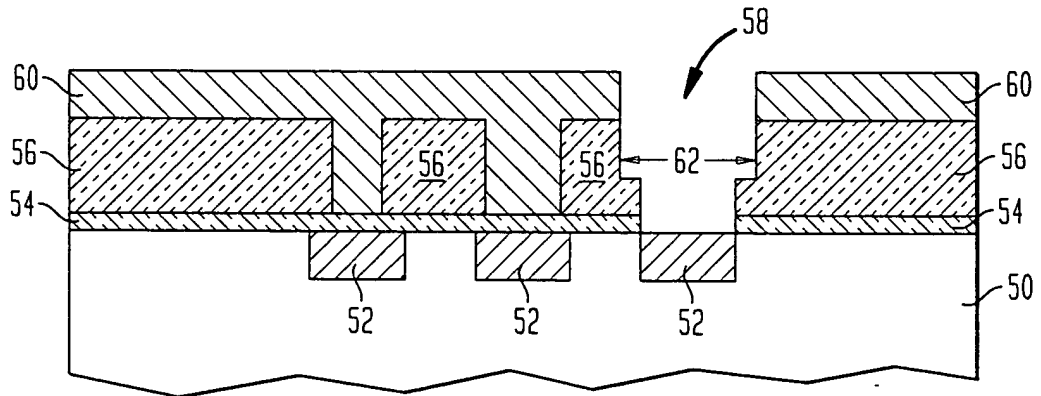


FIG. 2e



A cross-sectional view of a semiconductor device. The device consists of a substrate 50. On the substrate, there is a bottom layer 52. Above the bottom layer, there is a top layer 54. The top layer 54 is patterned into a series of rectangular blocks 64, which are separated by gaps 56. The top surface of the blocks 64 is also labeled 56. The bottom surface of the blocks 64 is labeled 54. The substrate 50 is shown with a wavy bottom edge.

This cross-sectional view shows a multi-layered structure. A central core (56) is composed of three stacked layers: a top layer (66), a middle layer (56), and a bottom layer (54). The core is flanked by side layers (64) on both the left and right. The entire assembly is supported by a base (50) which has a wavy bottom surface. The base is reinforced with three vertical pillars (52) and three horizontal pillars (72) that intersect the core layers.

FIG. 5

